



# SEMICONDUCTOR TECHNICAL DATA

## KMA010N20D

N-CH Trench MOSFET

### General Description

Switching regulator and DC-DC converter applications.

It's mainly suitable for power management in PC,  
portable equipment and battery powered systems.

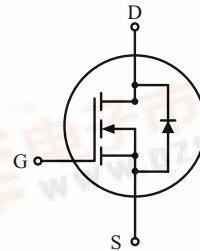
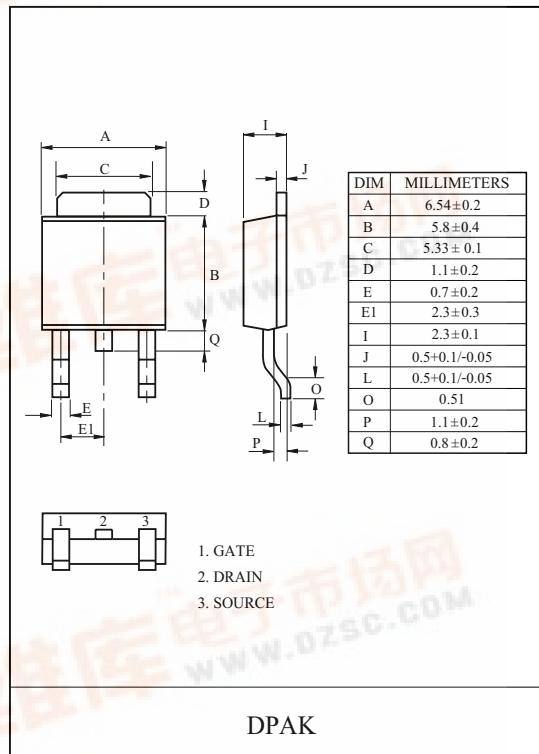
### FEATURES

- $V_{DSS}=20V$ ,  $I_D=10A$ .
- Drain-Source ON Resistnace.
- $R_{DS(ON)}=35m\Omega$  (Typ.) @  $V_{GS}=10V$ .
- $R_{DS(ON)}=45m\Omega$  (Typ.) @  $V_{GS}=4.5V$ .
- $R_{DS(ON)}=110m\Omega$  (Typ.) @  $V_{GS}=2.5V$ .
- Super high dense dell design.
- High power and current handing capability.

### MAXIMUM RATING ( $T_a=25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		$V_{DSS}$	20	V
Gate-Source Voltage		$V_{GSS}$	$\pm 16$	V
Drain Current	DC	$I_D$ *	10	A
	Pulsed	$I_{DP}$	25	
Drain Power Dissipation	$T_a=25^\circ C$	$P_D$ *	7.2	W
	$T_a=100^\circ C$		2.87	
Maximum Junction Temperature		$T_j$	150	°C
Storage Temperature Range		$T_{stg}$	-55~150	°C
Thermal Resistance, Junction to Ambient		$R_{thJA}$ *	17.4	°C/W

\* : Surface Mounted on FR4 Board,  $t \leq 10sec$ .



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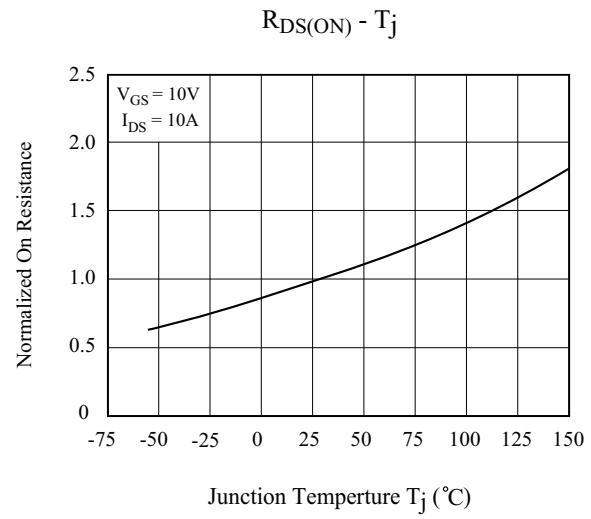
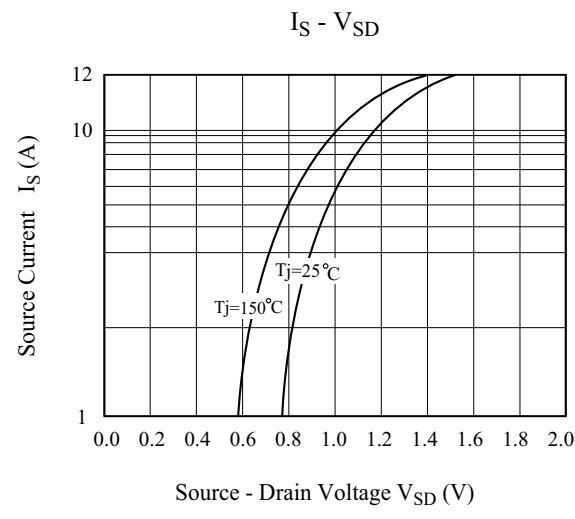
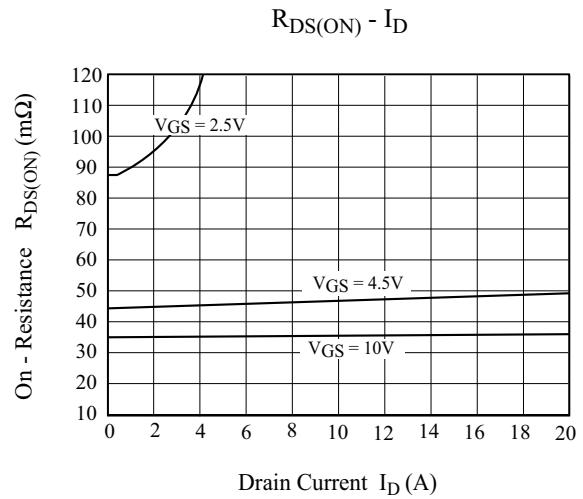
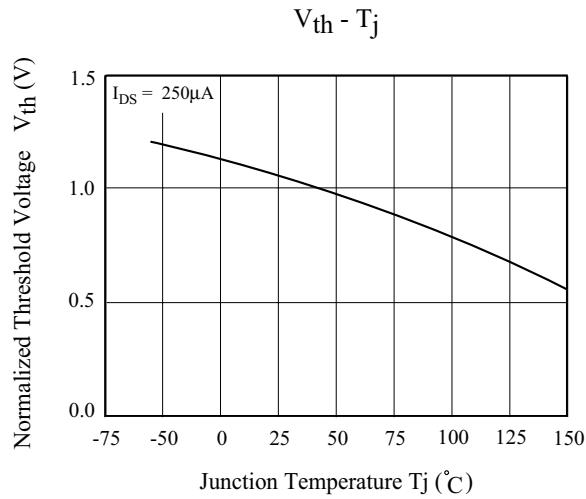
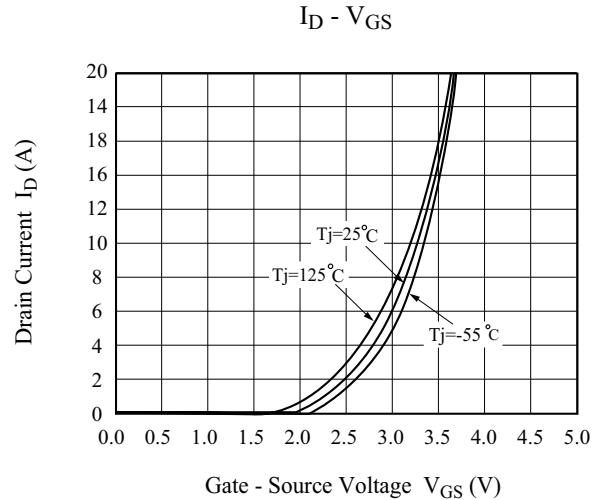
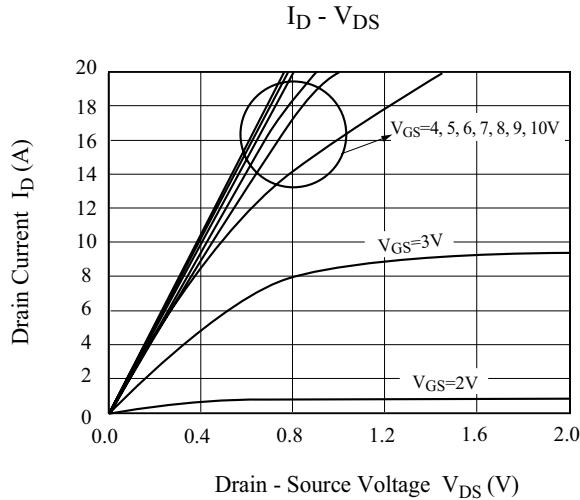
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V,	20	-	-	V
Drain Cut-off Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V,	-	-	1	μA
Gate Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.7	0.9	1.5	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V	-	-	±100	nA
Drain-Source ON Resistance	R <sub>DS(ON)</sub> <sup>(Note 1)</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	35	40	m Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A		45	54	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2A	-	110	130	
Source-Drain Diode Forward Voltage	V <sub>SD</sub> <sup>(Note 1)</sup>	I <sub>DR</sub> =6V, V <sub>GS</sub> =0V	-	0.7	1.3	V
<b>Dynamic</b> <sup>(Note 2)</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =10A V <sub>GS</sub> =4.5V (Fig.1)	-	6.0	8.4	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.9	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.3	-	
Turn-on Delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V R <sub>L</sub> =1.0 Ω R <sub>G</sub> =6 Ω (Fig.2)	-	10	15	ns
Turn-on Rise time	t <sub>r</sub>		-	50	75	
Turn-off Delay time	t <sub>d(off)</sub>		-	20	30	
Turn-off Fall time	t <sub>f</sub>		-	50	75	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	530	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	95	-	
Output Capacitance	C <sub>oss</sub>		-	160	-	

Note 1) Pulse test : Pulse width ≤300μs, duty cycle ≤2%

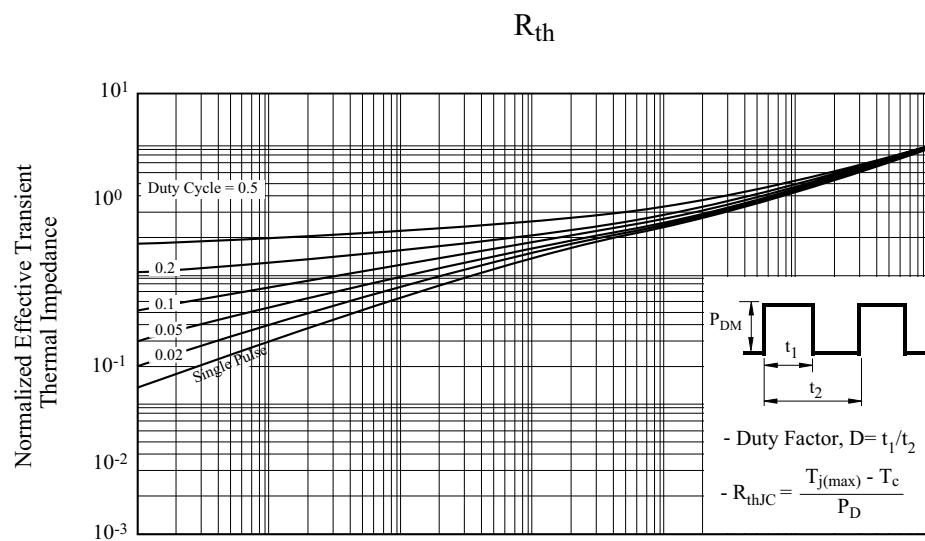
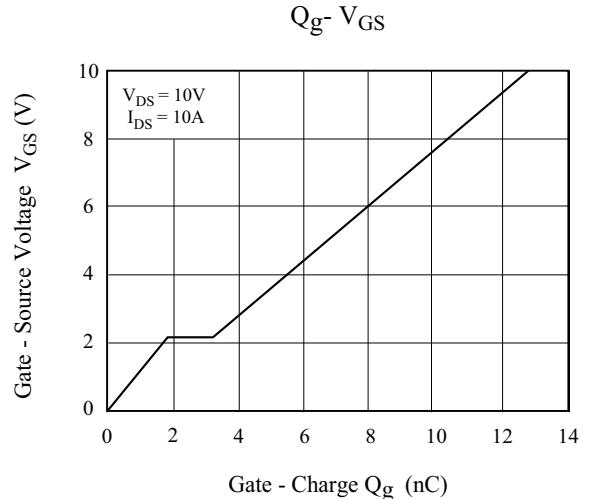
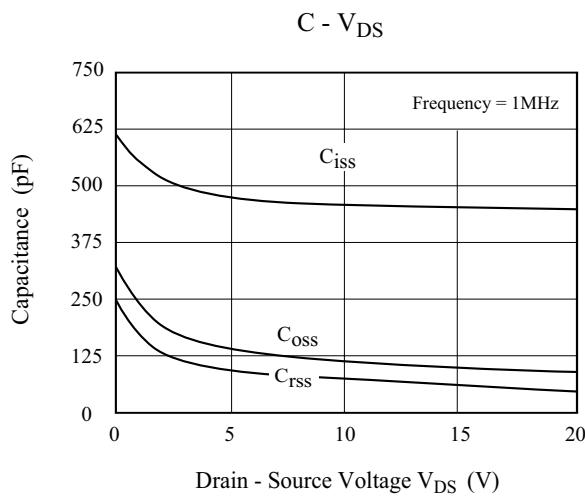
Note 2) Guaranteed by design, not subject to production testing.

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Fig. 1 Gate Charge

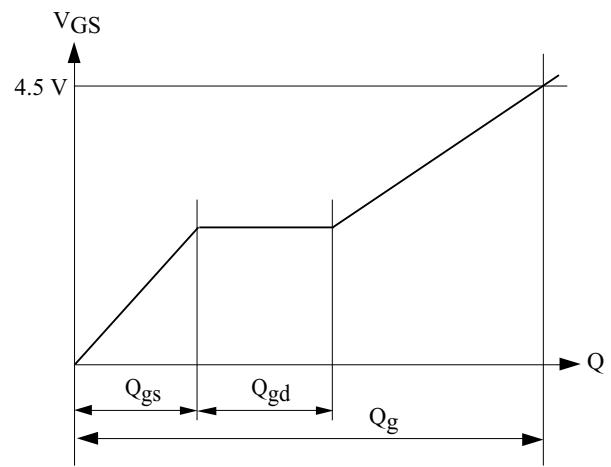
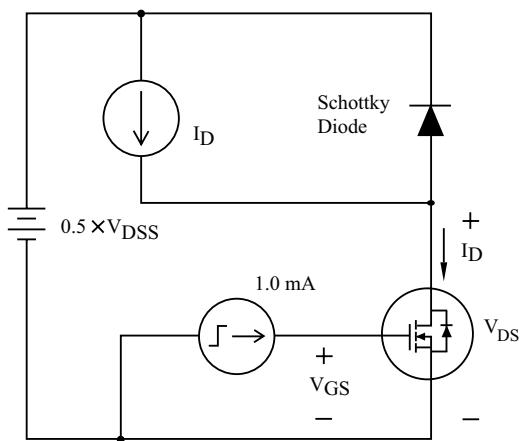


Fig. 2 Resistive Load Switching

